

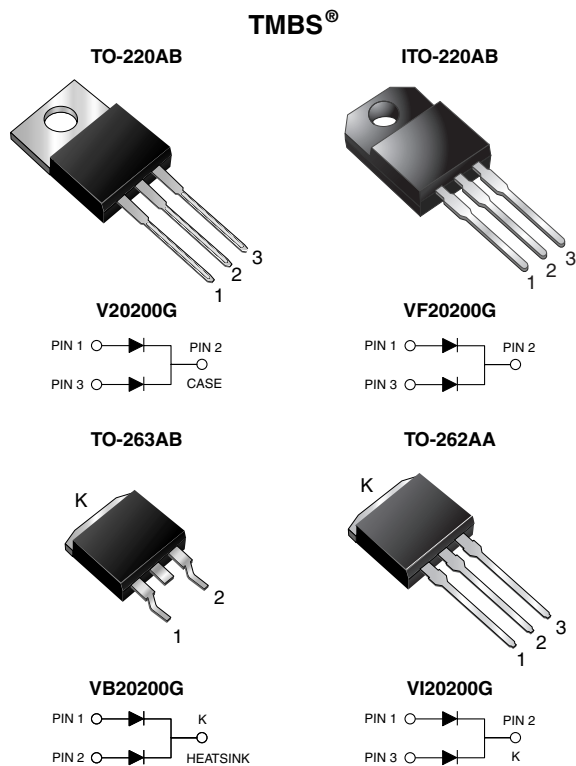


# V20200G, VF20200G, VB20200G & VI20200G

Vishay General Semiconductor

## Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.62\text{ V}$  at  $I_F = 5\text{ A}$



### FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Low thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

### MECHANICAL DATA

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS compliant, commercial grade

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	200 V
$I_{FSM}$	110 A
$V_F$ at $I_F = 10\text{ A}$	0.71 V
$T_J$ max.	150 °C

### MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V20200G	VF20200G	VB20200G	VI20200G	UNIT
Maximum repetitive peak reverse voltage	$V_{RRM}$		200			V
Maximum average forward rectified current (fig. 1) per device per diode	$I_{F(AV)}$		20 10			A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	$I_{FSM}$		110			A
Non-repetitive avalanche energy at $T_J = 25\text{ °C}$ , $L = 60\text{ mH}$ per diode	$E_{AS}$		60			mJ
Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$ , 1 kHz, $T_J = 38\text{ °C} \pm 2\text{ °C}$ per diode	$I_{RRM}$		0.5			A
Voltage rate of change (rated $V_R$ )	dV/dt		10 000			V/ $\mu\text{s}$
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$	$V_{AC}$		1500			V
Operating junction and storage temperature range	$T_J, T_{STG}$		- 40 to + 150			°C



ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>J</sub> = 25 °C	V <sub>BR</sub>	200 (minimum)	-	V
Instantaneous forward voltage per diode <sup>(1)</sup>	I <sub>F</sub> = 5 A	T <sub>J</sub> = 25 °C	V <sub>F</sub>	0.86	-	V
	I <sub>F</sub> = 10 A	T <sub>J</sub> = 25 °C		1.23	1.70	
Reverse current per diode <sup>(2)</sup>	V <sub>R</sub> = 180 V	T <sub>J</sub> = 25 °C	I <sub>R</sub>	1.9	-	μA
		T <sub>J</sub> = 125 °C		1.6	-	mA
	V <sub>R</sub> = 200 V	T <sub>J</sub> = 25 °C		-	150	μA
		T <sub>J</sub> = 125 °C		2.5	15	mA

Notes

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V20200G	VF20200G	VB20200G	VI20200G	UNIT
Typical thermal resistance per diode	R <sub>θJC</sub>	3.2	5.5	3.2	3.2	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V20200G-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	VF20200G-E3/4W	1.75	4W	50/tube	Tube
TO-263AB	VB20200G-E3/4W	1.39	4W	50/tube	Tube
TO-263AB	VB20200G-E3/8W	1.39	8W	800/reel	Tape and reel
TO-262AA	VI20200G-E3/4W	1.45	4W	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

(T<sub>A</sub> = 25 °C unless otherwise noted)

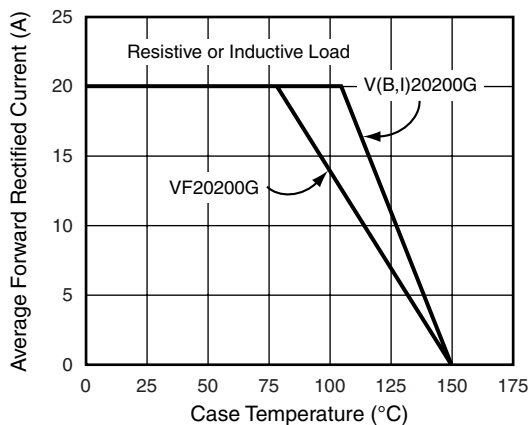


Figure 1. Maximum Forward Current Derating Curve

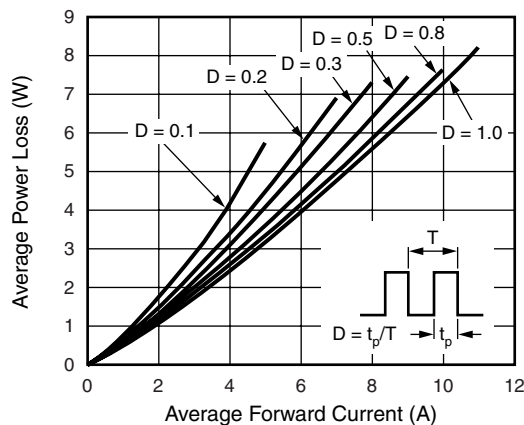


Figure 2. Forward Power Loss Characteristics Per Diode



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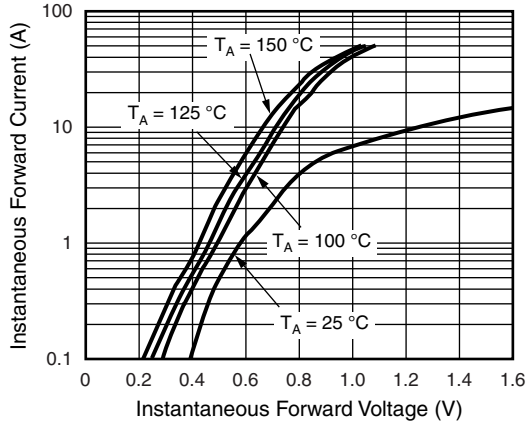


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

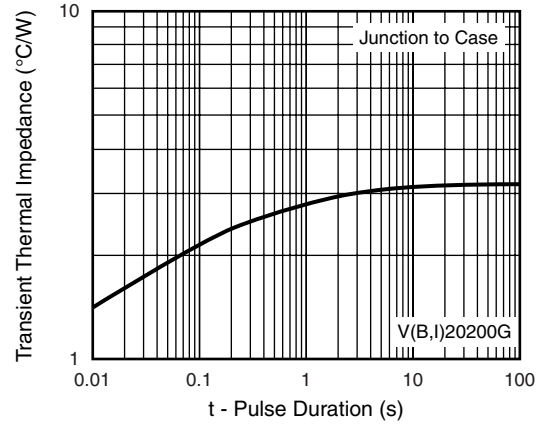


Figure 6. Typical Transient Thermal Impedance Per Diode

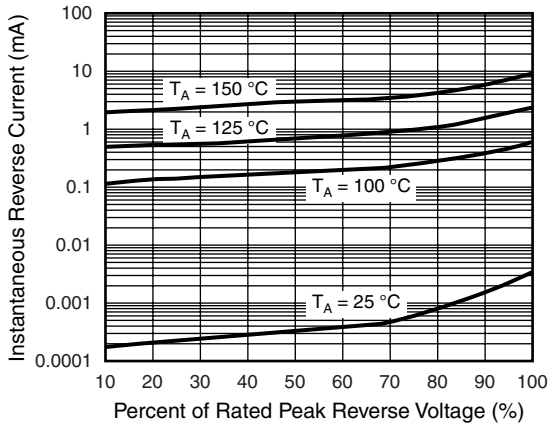


Figure 4. Typical Reverse Characteristics Per Diode

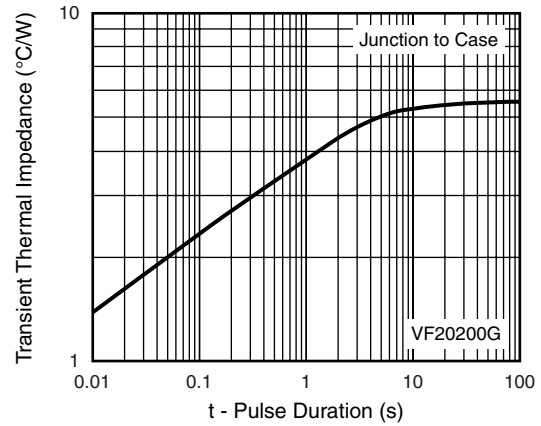


Figure 7. Typical Transient Thermal Impedance Per Diode

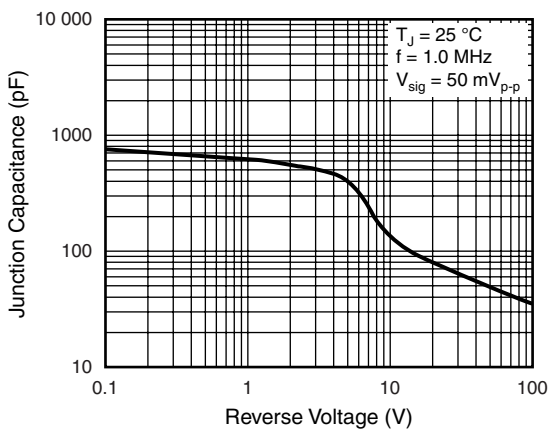


Figure 5. Typical Junction Capacitance Per Diode

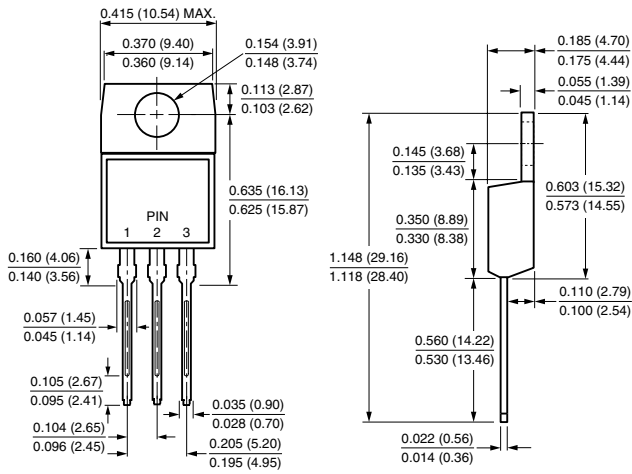
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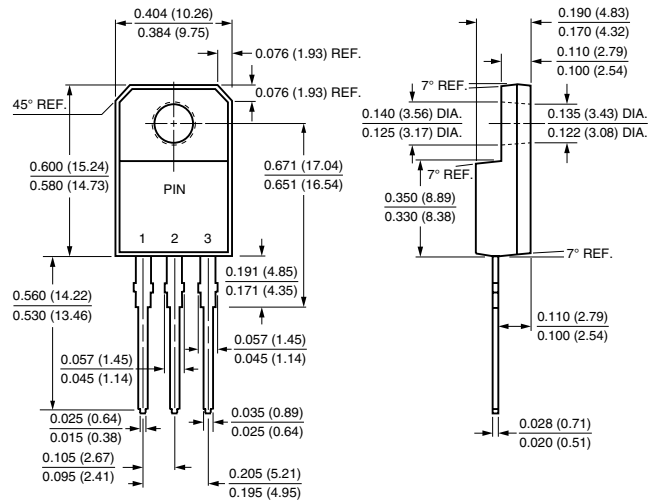


## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

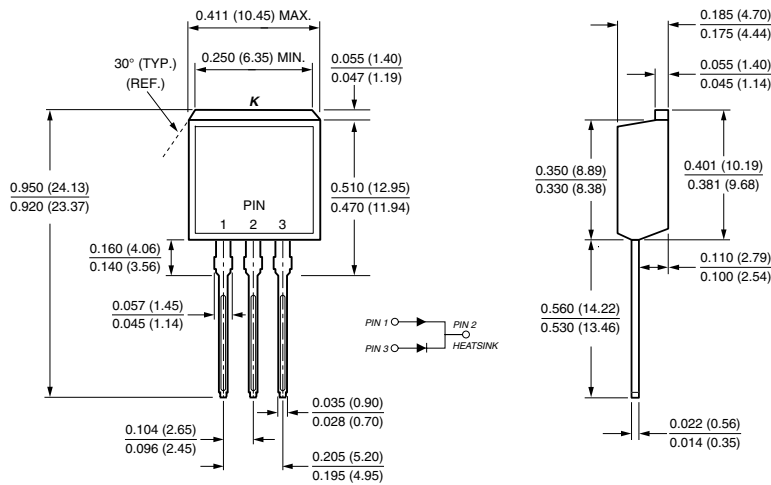
TO-220AB



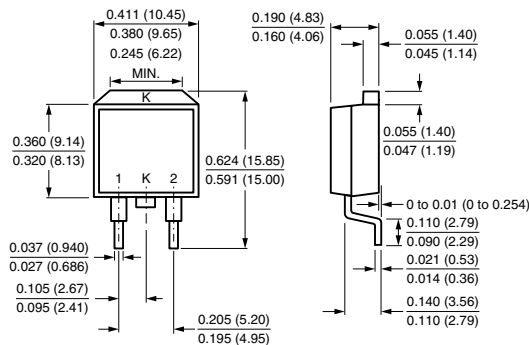
ITO-220AB



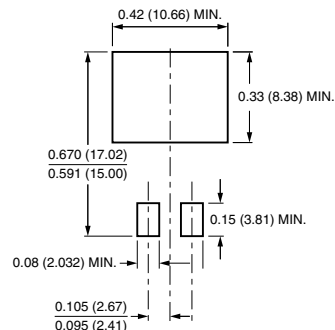
TO-262AA



TO-263AB



Mounting Pad Layout





## Disclaimer

All product specifications and data are subject to change without notice.

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